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FDP12N60NZ / FDPF12N60NZ N-Channel UniFETTM II MOSFET 600 V, 12 A, 650 m Ω

Features

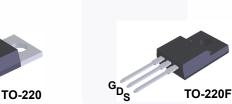
- $R_{DS(on)}$ = 530 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 6 A
- Low Gate Charge (Typ. 26 nC)
- Low C_{rss} (Typ. 12 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- ESD Improved Capability
- RoHS Compliant

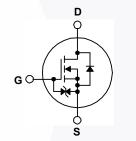
Applications

- LCD/ LED/ PDP TV
- Lighting
- Uninterruptible Power Supply

Description

UniFETTM II MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp balasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

	FDP12N60NZ	FDPF12N60NZ	Unit			
Drain to Source Voltage			6	V		
Gate to Source Voltage			±	V		
Drain Current	- Continuous (T _C = 25 ^o C)		12	12*	•	
Drain Current	- Continuous (T _C = 100 ^o C)		7.2	7.2*	A	
Drain Current	- Pulsed	48	48*	А		
Single Pulsed Avalanche Energy (Note 2)			5	mJ		
Avalanche Current		(Note 1)	12		А	
Repetitive Avalanche Energy		(Note 1)	24		mJ	
MOSFET dv/dt Ruggedness			20		V/ns	
Peak Diode Recovery dv/dt		(Note 3)	10		V/ns	
Deuver Dissignation	(T _C = 25°C)		240	39	W	
Fower Dissipation	- Derate Above 25°C		2.0	0.3	W/ºC	
Operating and Storage Temperature Range			-55 to	°C		
Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			3	°C		
	Gate to Source Voltage Drain Current Drain Current Single Pulsed Avalanche E Avalanche Current Repetitive Avalanche Ener MOSFET dv/dt Ruggednes Peak Diode Recovery dv/d Power Dissipation Operating and Storage Ter	Gate to Source Voltage Drain Current - Continuous ($T_C = 25^{\circ}C$) Drain Current - Pulsed Single Pulsed Avalanche Energy Avalanche Current Repetitive Avalanche Energy MOSFET dv/dt Ruggedness Peak Diode Recovery dv/dt Power Dissipation $(T_C = 25^{\circ}C)$ - Derate Above 25^{\circ}C Operating and Storage Temperature Range	$\begin{array}{c c c c c c c } \hline Drain to Source Voltage \\ \hline Gate to Source Voltage \\ \hline Gate to Source Voltage \\ \hline \\ \hline \\ Gate to Source Voltage \\ \hline \\ \hline \\ \hline \\ \\ \hline \\ Drain Current \\ \hline \\ \hline \\ \\ Drain Current \\ \hline \\ \hline \\ \\ \hline \\ \\ Drain Current \\ \hline \\ \\ \hline \\ \\ \hline \\ \\ \hline \\ \\ \\ \hline \\ \\ \\ \\ $	$\begin{array}{c c c c c c c } \hline Drain to Source Voltage & & & & & & & & & & & & & & & & & & &$	$\begin{array}{c c c c c c c } \hline Drain to Source Voltage & 600 \\ \hline Gate to Source Voltage & \pm 30 \\ \hline Gate to Source Voltage & & & & & & \\ \hline Gate to Source Voltage & & & & & & & \\ \hline Gate to Source Voltage & & & & & & & \\ \hline Drain Current & & & & & & \\ \hline Drain Current & & & & & & & & \\ \hline Drain Current & & & & & & & & \\ \hline Drain Current & & & & & & & & \\ \hline Drain Current & & & & & & & & \\ \hline Drain Current & & & & & & & & \\ \hline Pulsed & (Note 1) & 48 & & & & & & \\ \hline Single Pulsed Avalanche Energy & (Note 2) & & & & & \\ \hline Avalanche Current & & & & & & & & \\ \hline Avalanche Current & & & & & & & & \\ \hline Avalanche Current & & & & & & & & \\ \hline MOSFET dv/dt Ruggedness & & & & & & & & \\ \hline Peak Diode Recovery dv/dt & & & & & & & & & \\ \hline Power Dissipation & & & & & & & & \\ \hline \hline Power Dissipation & & & & & & & & \\ \hline \hline Cr = 25^{\circ}C) & & & & & & & & & \\ \hline Portent and Storage Temperature Range & & & & & & & \\ \hline \end{array}$	

*Drain current limited by maximum junction temperature

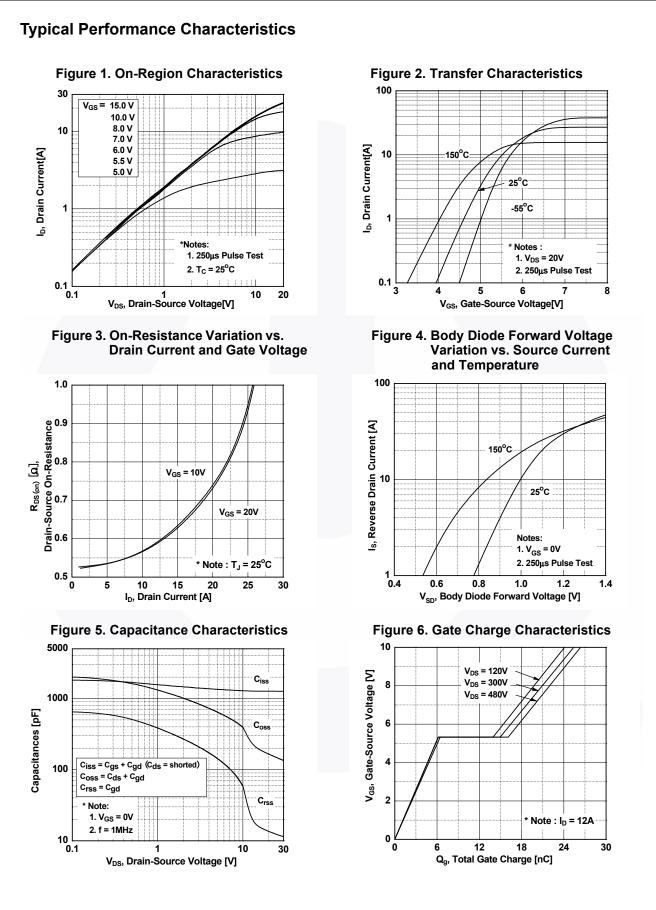
Thermal Characteristics

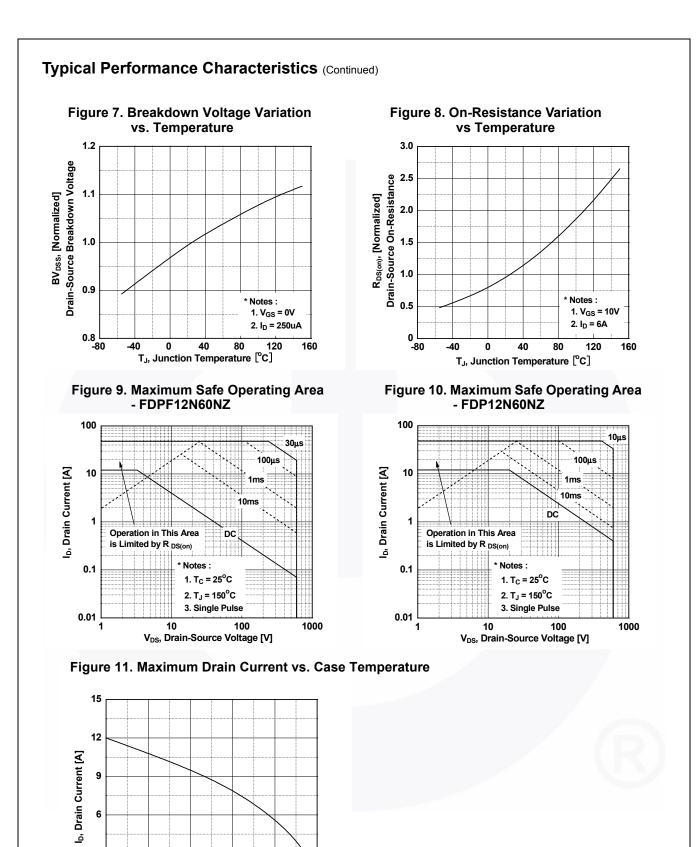
Symbol	Parameter	FDP12N60NZ	FDPF12N60NZ	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.52	3.2	°C/W	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	62.5	-0/00	

November 2013

Part Number Top Ma		Top Mark	Package	Packing Method	Reel Size) T	ape Width	Qu	antity	
FDP12N	FDP12N60NZ FDP12N60NZ		TO-220	Tube	N/A		N/A	50 units		
FDPF12			TO-220F	TO-220F Tube N/A		N/A		50 units		
Electrica	l Chara	acteristics T _C = 25°C	unless othe	erwise noted.						
Symbol		Parameter		Test Condition	s	Min.	Тур.	Max.	Unit	
- Off Charac	teristics				L. L. L.				1	
BV _{DSS}	Drain to	Source Breakdown Voltage	In =	250 μA, V _{GS} = 0 V, T	₁ = 25 ^o C	600	-	-	V	
ΔBV _{DSS} /ΔTJ		wn Voltage Temperature		$I_D = 250 \ \mu$ A, Referenced to 25° C		-	0.6	-	V/°C	
	7 0 1		V _{DS}	= 600 V, V _{GS} = 0 V		-	-	1		
DSS	Zero Gat	ero Gate Voltage Drain Current		$V_{DS} = 480 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$		-	-	10	μA	
I _{GSS}	Gate to E	Body Leakage Current	V _{GS}	s = ±30 V, V _{DS} = 0 V		-	-	±10	μΑ	
On Charac	teristics									
V _{GS(th)}		reshold Voltage	Ves	_S = V _{DS} , I _D = 250 μA		3	-	5	V	
R _{DS(on)}		ain to Source On Resistance		$s = 10 \text{ V}, I_D = 6 \text{ A}$		-	0.53	0.65	Ω	
9FS	Forward	Transconductance		_s = 20 V, I _D = 6 A		-	13.5	-	S	
Dynamic C	Characte	ristics								
C _{iss}	1	pacitance				-	1260	1676	pF	
C _{oss}		apacitance		$_{\rm S} = 25 \text{ V}, \text{ V}_{\rm GS} = 0 \text{ V},$	-	150	200	pF		
C _{rss}		Transfer Capacitance	t = 1	f = 1 MHz		-	12	18	pF	
Q _{g(tot)}		e Charge at 10V	V	V _{DS} = 480 V, I _D = 12 A, V _{GS} = 10 V (Note 4)		-	26	34	nC	
Q _{gs}		Source Gate Charge				-	6	-	nC	
Q _{gd}	Gate to D	Drain "Miller" Charge	0			-	10	-	nC	
Switching	Charact	eristics								
t _{d(on)}	-	Delay Time		V _{DD} = 300 V, I _D = 12 A,		-	25	60	ns	
t _r		Rise Time	VDD			-	50	110	ns	
t _{d(off)}		Delay Time	V _{GS}	$_{\rm S}$ = 10 V, R _G = 25 Ω	-		80	170	ns	
t _f		Fall Time			(Note 4)		60	130	ns	
Drain-Sou	rce Diod	e Characteristics					11			
I _S	1	Continuous Drain to Source	e Diode For	ward Current			_	12	А	
I _{SM}	Maximum Pulsed Drain to Source Diode Fo					-	_	48	A	
V _{SD}	Drain to Source Diode Forward Voltage			$V_{GS} = 0 V, I_{SD} = 12 A$		-	-	1.4	V	
t _{rr}		Recovery Time		$V_{GS} = 0 V, I_{SD} = 12 A,$		-	350	· • ·	ns	
Q _{rr}	Reverse Recovery Charge			$dI_{\rm F}/dt = 100 \text{ A}/\mu \text{s}$		-	2.2	-	μC	

2





T_c, Case Temperature [°C]

100

125

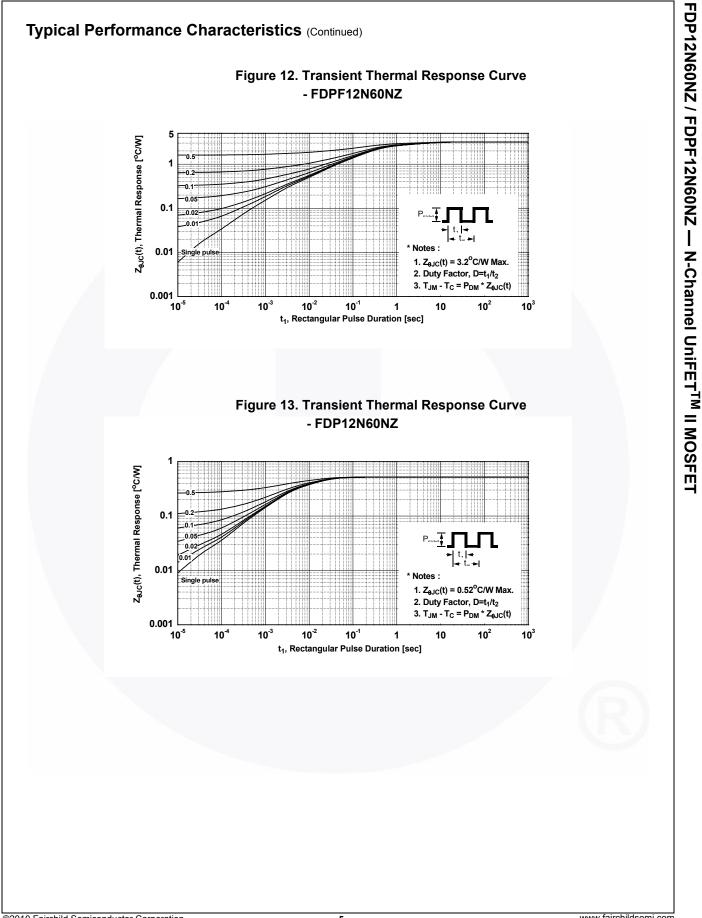
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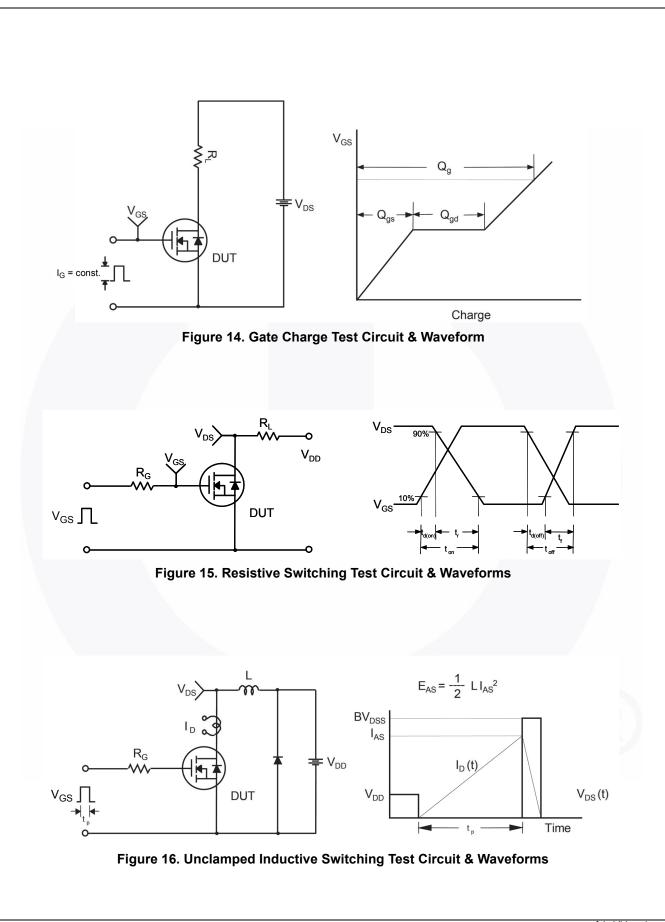
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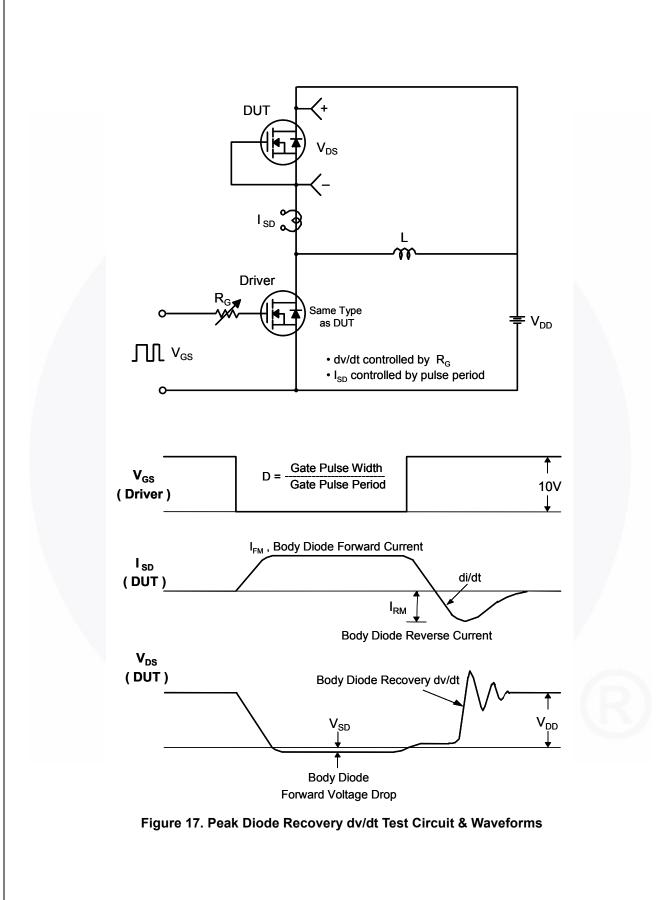
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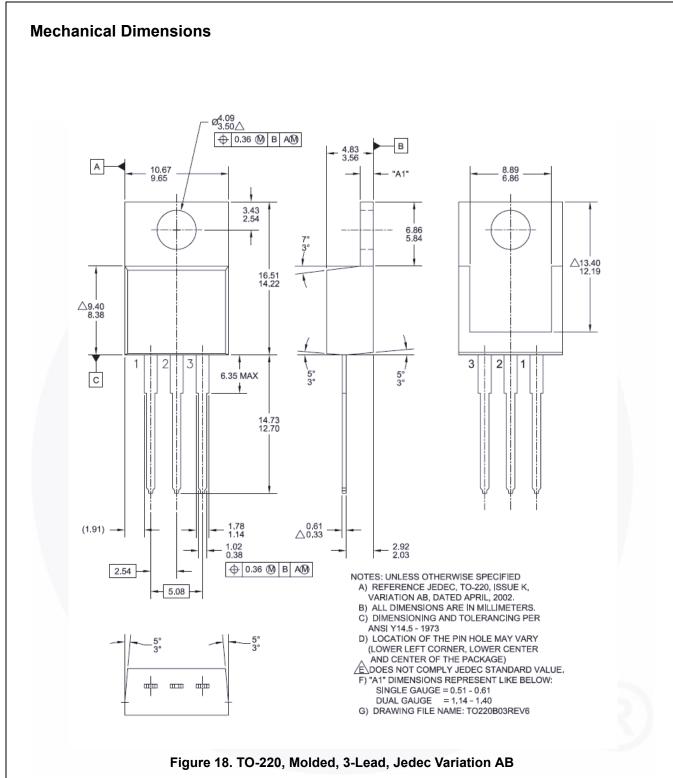
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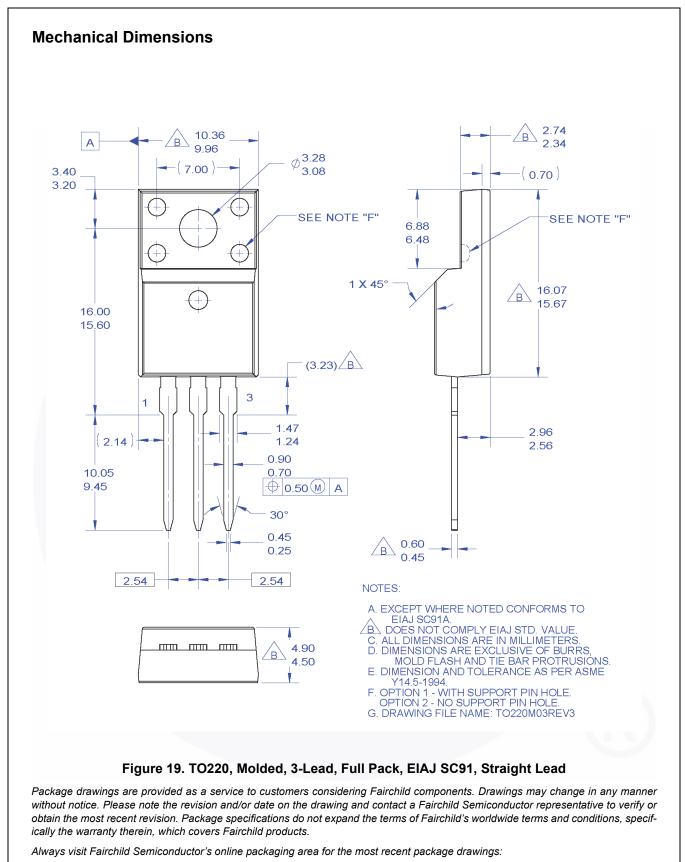


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FDP12N60NZ / FDPF12N60NZ — N-Channel UniFETTM II MOSFET



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FDP12N60NZ / FDPF12N60NZ —

N-Channel UniFETTM II MOSFET



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